

Title (en)  
ORGANIC FIELD EFFECT TRANSISTOR WITH A PHOTOSTRUCTURED GATE DIELECTRIC, METHOD FOR THE PRODUCTION AND USE THEREOF IN ORGANIC ELECTRONICS

Title (de)  
ORGANISCHER FELDEFFEKT-TRANSISTOR MIT FOTOSTRUKTURIERTEM GATE-DIELEKTRIKUM, EIN VERFAHREN ZU DESSEN ERZEUGUNG UND DIE VERWENDUNG IN DER ORGANISCHEN ELEKTRONIK

Title (fr)  
TRANSISTOR A EFFET DE CHAMP ORGANIQUE A DIELECTRIQUE DE GRILLE PHOTOSTRUCTURE, SON PROCEDE DE PRODUCTION ET SON UTILISATION EN ELECTRONIQUE ORGANIQUE

Publication  
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Application  
**EP 02706645 A 20020129**

Priority  

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- DE 10105914 A 20010209

Abstract (en)  
[origin: WO02065557A1] The invention relates to an organic field effect transistor which is especially characterized by a cross-linked, structured insulating layer (4) on which the gate electrode (5) is arranged. The structure of the OFET ensures that the gate electrode (5) of an OFET can be used as a strip conductor to the source electrode (2) of the next transistor and can be used in the construction of larger circuits. .

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IPC 8 full level  
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Cited by  
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